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17. (New) A method of operating a DMOS transistor comprising diverting current from a source of the DMOS transistor with a Schottky diode that is co-integrated with the DMOS transistor when the source becomes more positive than a drain of the DMOS transistor.

*P. 13, 14
Fig. 18*

18. (New) The method of claim 17 wherein [the act of diverting current from a source of the DMOS transistor] includes diverting current from a parasitic bipolar transistor having a collector coupled to a substrate in which both the DMOS transistor and the Schottky diode are integrated.

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P. 14*

19. (New) The method of claim 17 wherein [the act of diverting current from a source of the DMOS transistor with a Schottky diode includes diverting current from a p-n junction body diode] having a cathode coupled to the drain and an anode coupled to the source.

20. (New) The method of claim 17 wherein [the act of diverting current from a source of the DMOS transistor] with a Schottky diode includes diverting current from the source with a Schottky diode having a cathode coupled to the drain and an anode coupled to the source.

REMARKS

Claims 17-20 are now pending in the present application. Favorable consideration and a Notice of Allowance are earnestly solicited.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADEIn the Specification:

Amend the specification by inserting a new section before the "Technical Field" as follows:

This application is a Continuation of pending United States Patent Application No. 09/243,017, filed February 3, 1999, which is a Divisional of United States Patent No. 5,925,910, issued July 20, 1999.--

In the Claims:

Claim 1-16 have been canceled.

New claims 17-20 have been added as follows:

17. (New) A method of operating a DMOS transistor comprising diverting current from a source of the DMOS transistor with a Schottky diode that is co-integrated with the DMOS transistor when the source becomes more positive than a drain of the DMOS transistor.

18. (New) The method of claim 17 wherein the act of diverting current from a source of the DMOS transistor includes diverting current from a parasitic bipolar transistor having a collector coupled to a substrate in which both the DMOS transistor and the Schottky diode are integrated.

19. (New) The method of claim 17 wherein the act of diverting current from a source of the DMOS transistor with a Schottky diode includes diverting current from a p-n junction body diode having a cathode coupled to the drain and an anode coupled to the source.

20. (New) The method of claim 17 wherein the act of diverting current from a source of the DMOS transistor with a Schottky diode includes diverting current from the source with a Schottky diode having a cathode coupled to the drain and an anode coupled to the source.